Title (en)

LOCAL INTERCONNECT USING A MATERIAL COMPRISING TUNGSTEN

Publication

**EP 0463373 A3 19920325 (EN)**

Application

**EP 91108472 A 19910524**

Priority

US 54619390 A 19900629

Abstract (en)

[origin: EP0463373A2] A tungsten silicide interconnect (28) is formed on device (14) as a local interconnect between devices. The tungsten silicide interconnect (28) provides several advantages over prior art methods, such as titanium nitride or polysilicon local interconnects. <IMAGE>

IPC 1-7

**H01L 21/90**; H01L 23/532

IPC 8 full level

**H01L 21/28** (2006.01); **H01L 21/308** (2006.01); **H01L 21/3205** (2006.01); **H01L 21/3213** (2006.01); **H01L 21/768** (2006.01); **H01L 23/52** (2006.01); **H01L 23/532** (2006.01); **H01L 29/43** (2006.01)

CPC (source: EP)

**H01L 21/32136** (2013.01); **H01L 21/76889** (2013.01); **H01L 21/76895** (2013.01); **H01L 23/53257** (2013.01); H01L 2924/0002 (2013.01)

Citation (search report)

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